

General Description

GL4N65FA9, the silicon N-channel Enhanced VDMOSFET, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220F, which accords with the RoHS standard.

Features

- Fast Switching
- ESD Improved Capability
- Low ON Resistance(Typical Data:1.9Ω)
- Low Gate Charge (Typical Data:14.5nC)
- Low Reverse transfer capacitances(Typical:8.5pF)
- 100% Single Pulse avalanche energy Test

Applications

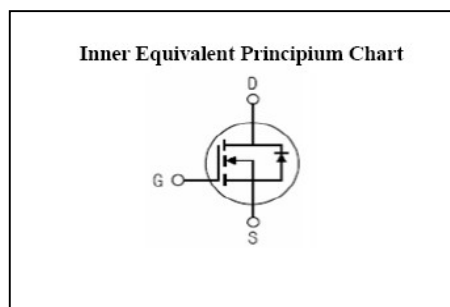
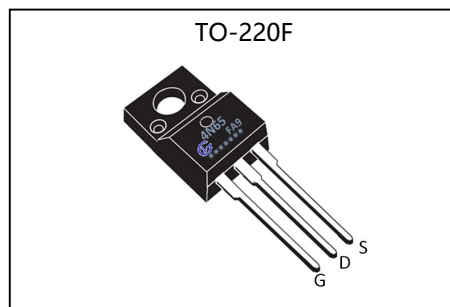
- Power switch circuit of adaptor and charger

Absolute (Tc= 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	650	V
I_D	Continuous Drain Current	4	A
	Continuous Drain Current $T_C = 100^\circ\text{C}$	3.2	A
I_{DM}^{a1}	Pulsed Drain Current	16	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	280	mJ
E_{AR}^{a1}	Avalanche Energy ,Repetitive	30	mJ
I_{AR}^{a1}	Avalanche Current	2.5	A
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	30	W
	Derating Factor above 25°C	0.24	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	300	$^\circ\text{C}$

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device.

$V_{DSS}(T_C=150^\circ\text{C})$	650	V
I_D	4	A
$P_D(T_C=25^\circ\text{C})$	30	W
$R_{DS(ON)typ}$	1.9	Ω





GL4N65FA9

GL Silicon N-Channel Power MOSFET

Electrical Characteristics (Tc= 25°C unless otherwise specified)

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	650	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu A$, Reference 25°C	--	0.67	--	V/°C
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=650V, V_{GS}=0V, T_a=25^\circ C$	--	--	1	μA
		$V_{DS}=520V, V_{GS}=0V, T_a=125^\circ C$	--	--	100	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+30V$	--	--	1	μA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-30V$	--	--	-1	μA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=2.0A$	--	1.9	2.4	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	--	4.0	V
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	$V_{DS}=15V, I_D=2.0A$	--	3.5	--	S
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=25V$ $f=1.0MHz$	--	544	--	pF
C_{oss}	Output Capacitance		--	55	--	
C_{rss}	Reverse Transfer Capacitance		--	8.5	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=4.0A, V_{DD}=325V$ $R_g=4.7\Omega$	--	10	--	ns
t_r	Rise Time		--	11	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	31	--	
t_f	Fall Time		--	14	--	
Q_g	Total Gate Charge	$I_D=4.0A, V_{DD}=325V$ $V_{GS}=10V$	--	13	--	nC
Q_{gs}	Gate to Source Charge		--	3.4	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	2.7	--	



GL4N65FA9

GL Silicon N-Channel Power MOSFET

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	4	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	16	A
V_{SD}	Diode Forward Voltage	$I_S=4.0A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=4.0A, T_J=25^{\circ}C$	--	430	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt=100A/us, V_{GS}=0V$	--	1270	--	uC
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

Thermal Characteristics

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	4.17	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-Ambient	100	$^{\circ}C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=10.0mH, I_D=7.6A$, Start $T_J=25^{\circ}C$

^{a3}: $I_{SD}=4A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}$, Start $T_J=25^{\circ}C$

Characteristics Curves

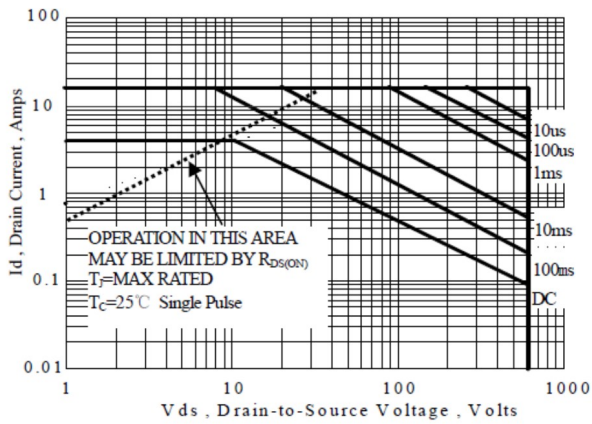


Figure 1 Maximum Forward Bias Safe Operating Area

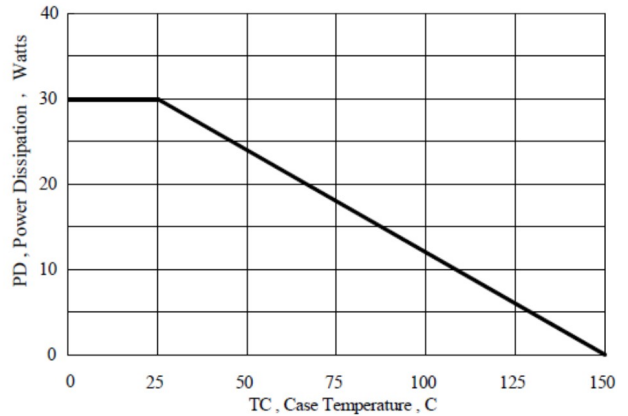


Figure 2 Maximum Power Dissipation vs Case Temperature

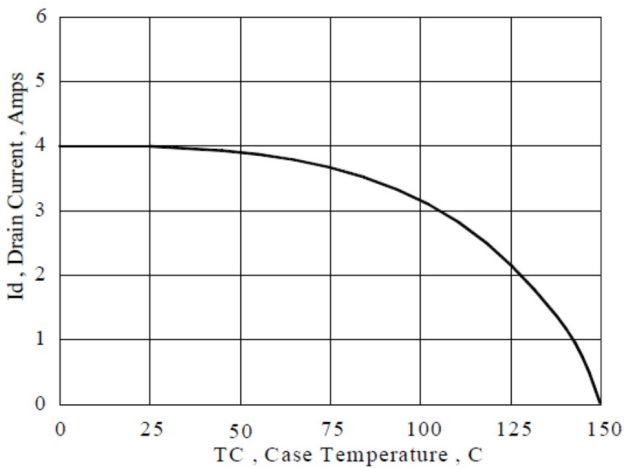


Figure 3 Maximum Continuous Drain Current vs Case Temperature

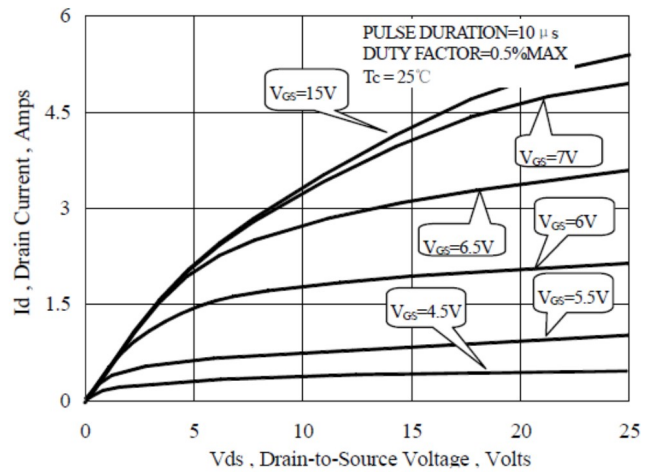


Figure 4 Typical Output Characteristics

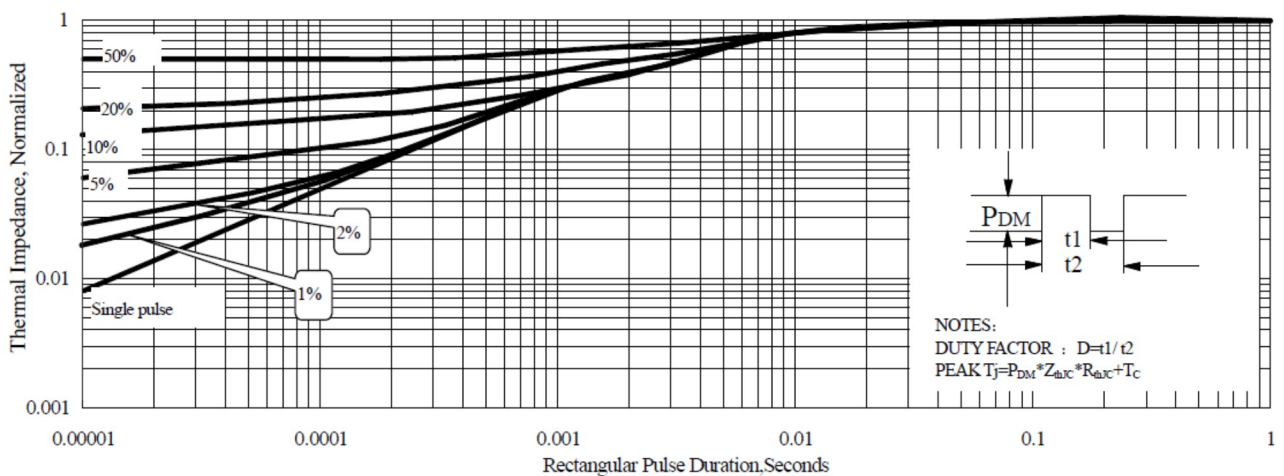


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

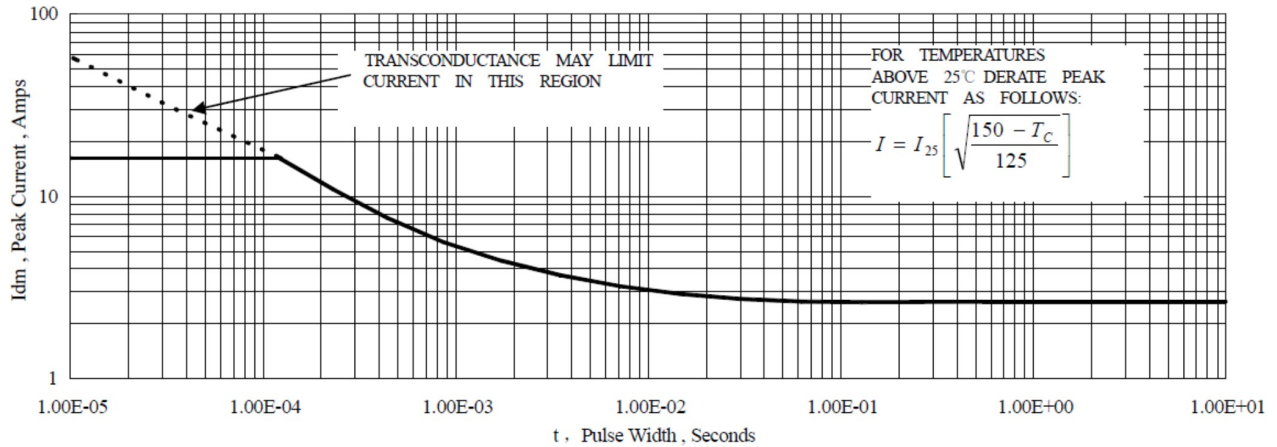


Figure 6 Maximum Peak Current Capability

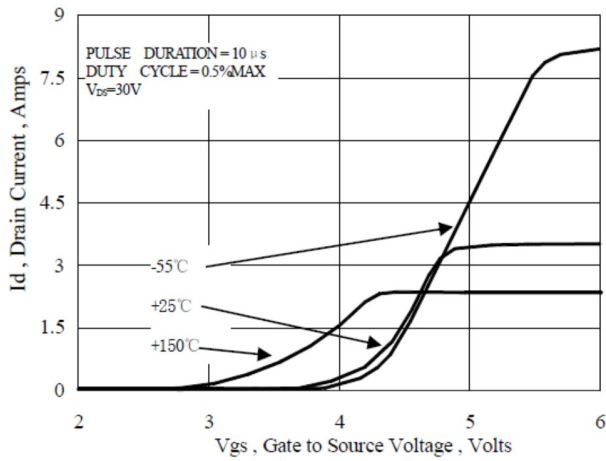


Figure 7 Typical Transfer Characteristics

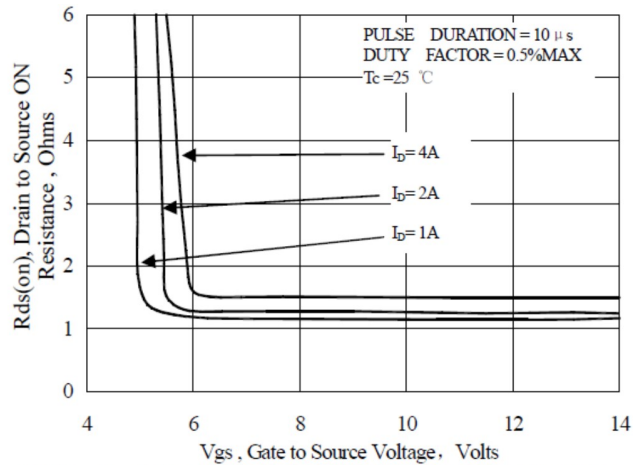


Figure 8 Typical Drain to Source ON Resistance vs Gate Voltage and Drain Current

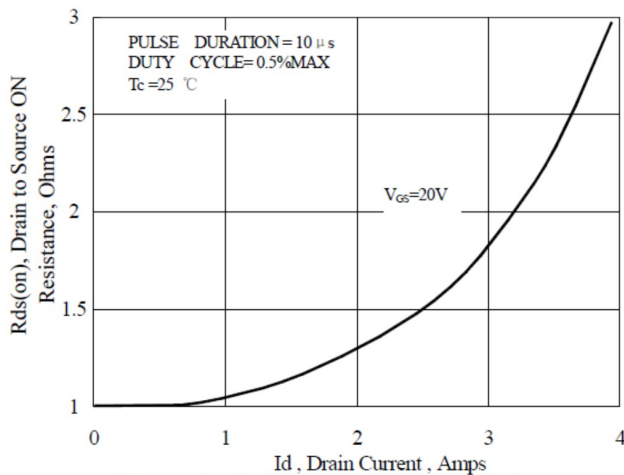


Figure 9 Typical Drain to Source ON Resistance vs Drain Current

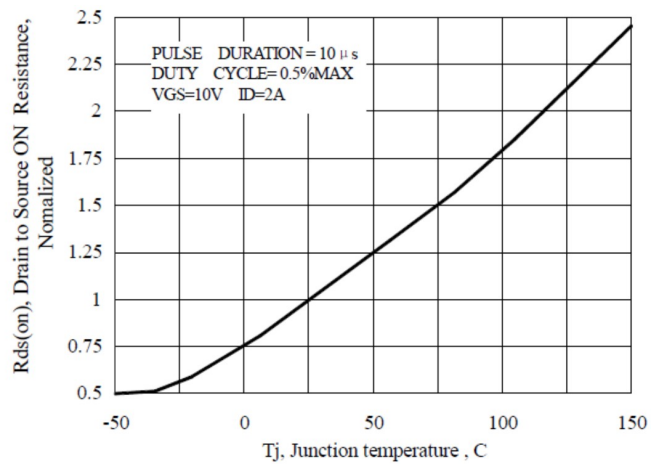


Figure 10 Typical Drain to Source on Resistance vs Junction Temperature

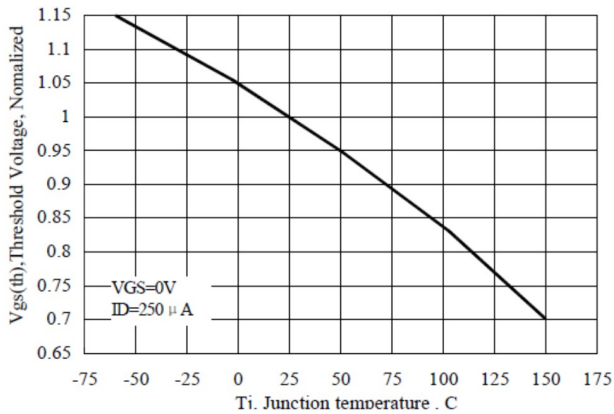


Figure 11 Typical Threshold Voltage vs Junction Temperature

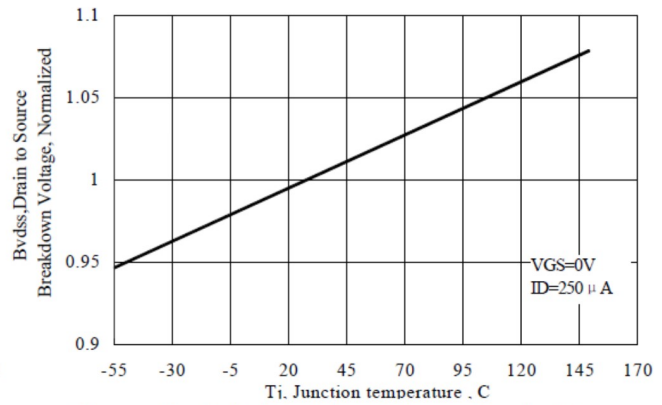


Figure 12 Typical Breakdown Voltage vs Junction Temperature

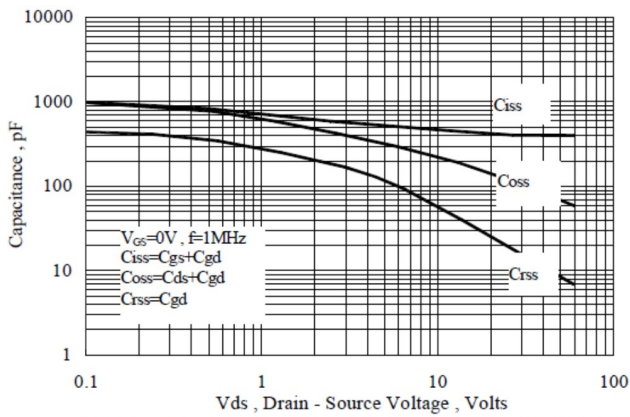


Figure 13 Typical Capacitance vs Drain to Source Voltage

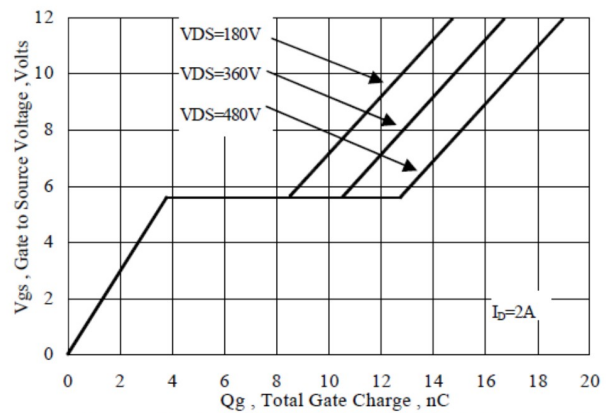


Figure 14 Typical Gate Charge vs Gate to Source Voltage

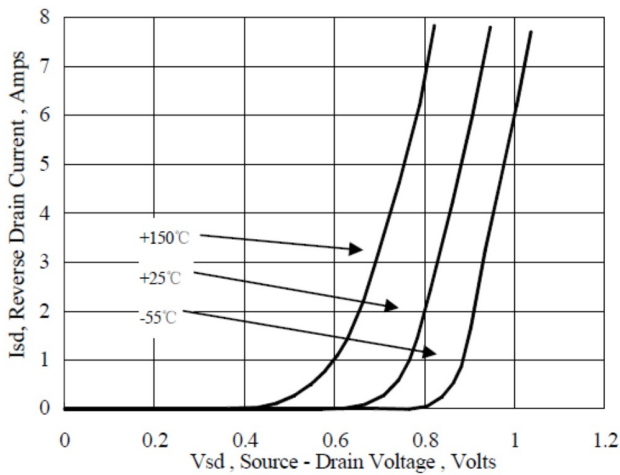


Figure 15 Typical Body Diode Transfer Characteristics

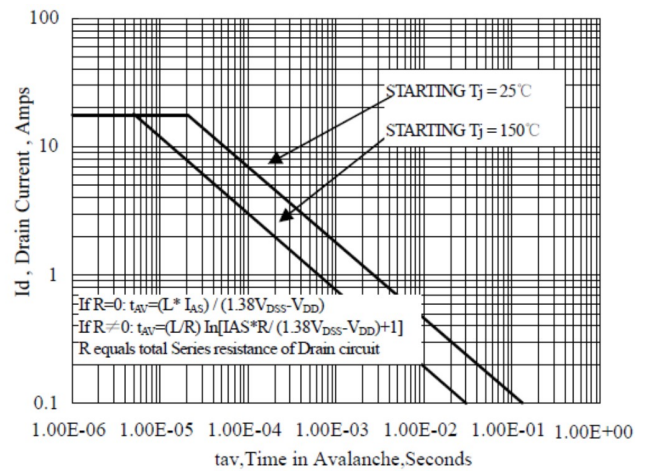


Figure 16 Unclamped Inductive Switching Capability